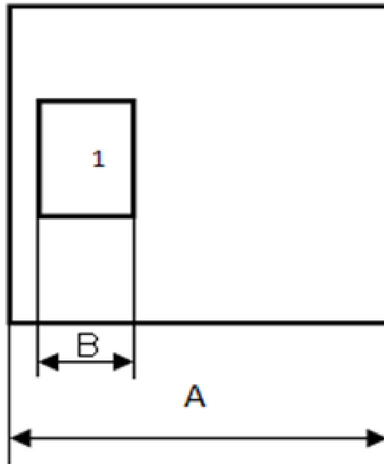
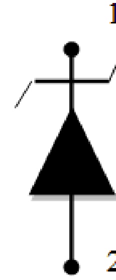
mikron VSP-MIKRON





Mechanical data: A_x= 290 um, A_y=290um,
B_x=B_y=80 um

Schematic and pinning diagram

Chip thickness: 138+/-12um on 4” wafer
Scribe Line width - 40um
Top Metal – Pin 1: Al metallization for wire bonding
Backside – Pin 2: Ti-Ni-Ag for soldering
Probing: sampling testing: no bad dice inking guaranteed good dice quantity≥93%

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Peak pulse power	P_{PP}	8/20 µS pulse per diode	100*	W
Peak pulse current	I_{PP}	8/20 µS pulse per diode	5*	A
Electrostatic Discharge	ESD	IEC 61000-4-2, level 4 (ESD)	>15 (air); >8 (contact)	kV
Max.junction temperature	T_j		150	ºC

Characteristics (Ta=25ºC)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Stand-Off Voltage	V_{RWM}		-	-	5.0	V
Reverse leakage current	I_R	V_R=+5.0V	-	-	1.0	µA
Breakdown voltage	V_{BR}	I=1mA	6.0	7.0	-	V
Forward voltage	V_F	I_F=15mA	-	-	1.15	V
Clamping Voltage	V_{CL}	I_{PP}=1A, t=8/20µS; I_{PP}=5A, t=8/20µS	- -	- -	10.0* 20.0*	V
Capacitance	C_j	V_R=0V; f=1MHz	-	0,5	0,7	pF

*- For Device testing